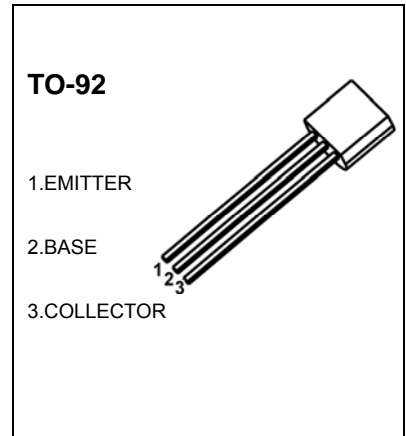


TO-92 Plastic-Encapsulate Transistors

2N5400 TRANSISTOR (PNP)

FEATURE

- **Switching and Amplification in High Voltage**
Applications such as Telephony
- **Low Current(max. 600mA)**
- **High Voltage(max.130v)**



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-130	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-0.6	A
P _C	Collector Power Dissipation	0.625	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-130			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-120			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -100 V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -3 V, I _C =0			-0.1	μA
DC current gain	h _{FE1}	V _{CE} = -5 V, I _C =-1mA	30			
	h _{FE2}	V _{CE} = -5 V, I _C = -10mA	40		180	
	h _{FE3}	V _{CE} = -5 V, I _C =-50mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA			-0.2	V
	V _{CE(sat)}	I _C = -50mA, I _B = -5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -10mA, I _B = -1mA			-1	V
	V _{BE(sat)}	I _C = -50mA, I _B = -5mA			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-10mA f =30MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			6	pF